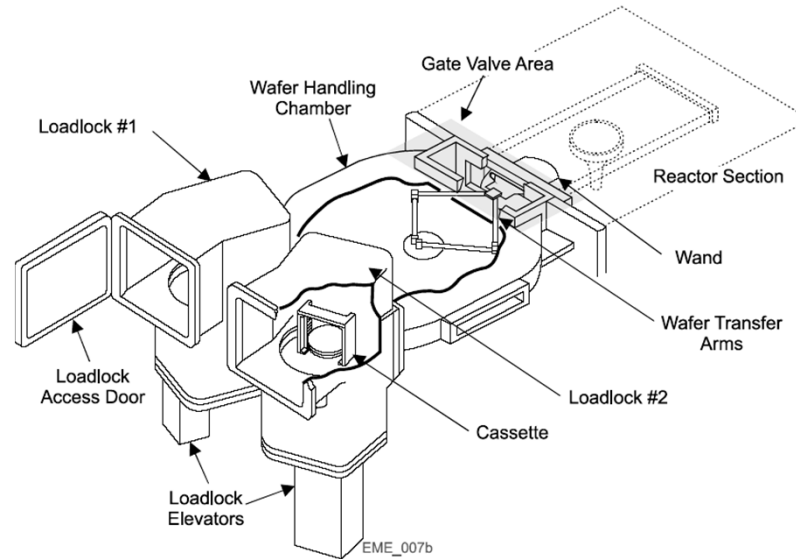


四族磊晶機台(RDT005)



The process gases:

1. H₂
2. DCS (SiH₂Cl₂)
3. GeH₄ (10% in H₂)
4. B₂H₆ (1% in H₂, p-type)
5. PH₃ (10% in H₂, n-type)
6. HCl

The wafer can be processed:

Standard 8 inch wafer, one wafer per run

Can not process broken wafers

The layers can be grown:

Si (DCS, 825°C)

SiGe (DCS, GeH₄, 600~700°C)

Ge (375-400°C, 40Torr)